

ABSTRACT OF THE DISCLOSURE

A method of forming a CMOS transistor on a substrate is provided, wherein the method requires only two implanting procedures to form all source/drain and light doped region. First, the source/drain of an NMOS transistor is formed by using a photoresist layer which covers up the source/drain of a PMOS transistor as a mask with a phosphorus dopant being implanted into. Next, the lightly doped region of an NMOS transistor and the source/drain of a PMOS transistor are formed by using a photoresist layer which covers up the source/drain of an NMOS transistor as well as the gate 5 as masks with a boron dopant being implanted into. Of which, the dosage of the boron dopant is smaller than that of the phosphorus dopant.

10

* * * * *